

2SK1540(L), 2SK1540(S)

Silicon N Channel MOS FET

REJ03G0952-0200

(Previous: ADE-208-1292)

Rev.2.00 Sep 07, 2005

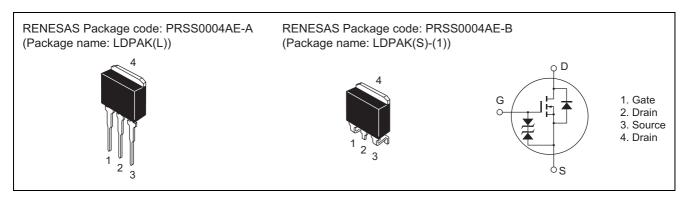
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	450	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	7	А
Drain peak current	I _{D(pulse)} *1	28	А
Body to drain diode reverse drain current	I _{DR}	7	А
Channel dissipation	Pch*2	60	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at $T_C = 25$ °C

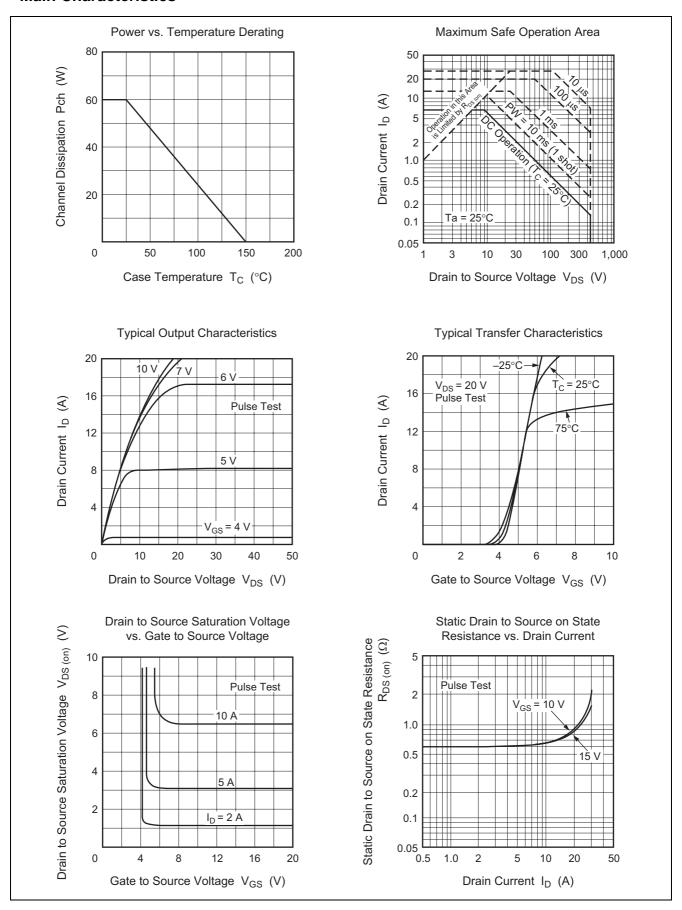
Electrical Characteristics

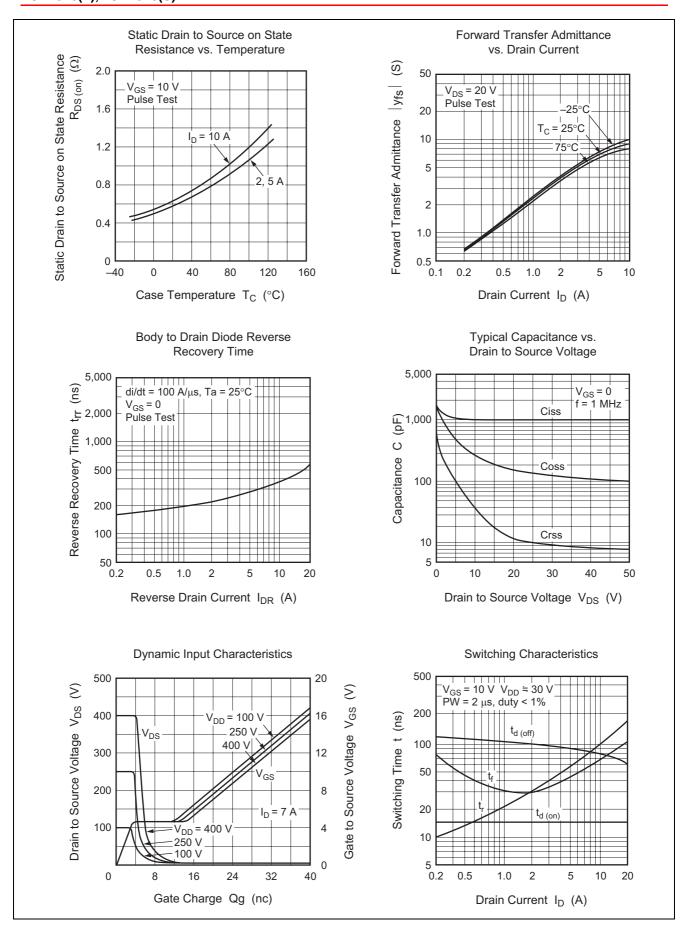
 $(Ta = 25^{\circ}C)$

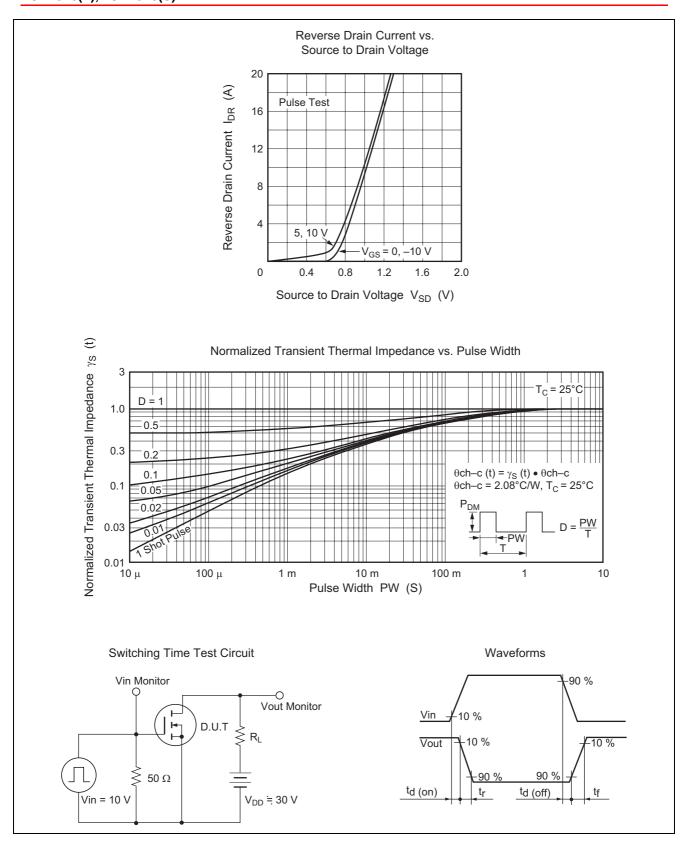
Item	Symbol	Min	Тур	Max	Unit	Test conditions	
Drain to source breakdown voltage	$V_{(BR)DSS}$	450	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
Gate to source breakdown voltage	V _{(BR)GSS}	±30	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$	
Gate to source leak current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$	
Zero gate voltage drain current	I _{DSS}	_	_	250	μΑ	$V_{DS} = 360 \text{ V}, V_{GS} = 0$	
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	_	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$	
Static drain to source on state	R _{DS(on)}	_	0.6	0.8	Ω	$I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}^{*3}$	
resistance	lv. l	4.0	6.5		S	1 4 4 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	
Forward transfer admittance	y _{fs}	4.0	6.5	_		$I_D = 4 \text{ A}, V_{DS} = 10 \text{ V}^{*3}$	
Input capacitance	Ciss	_	1050	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$	
Output capacitance	Coss	_	280	_	pF	f = 1 MHz	
Reverse transfer capacitance	Crss	_	40	_	pF		
Turn-on delay time	t _{d(on)}	_	15	_	ns	$I_D = 4 A$, $V_{GS} = 10 V$,	
Rise time	t _r	_	55	_	ns	$R_L = 7.5 \Omega$	
Turn-off delay time	t _{d(off)}	_	95	_	ns		
Fall time	t _f	_	40	_	ns	\neg	
Body to drain diode forward voltage	V_{DF}	_	0.95	_	V	$I_F = 7 \text{ A}, V_{GS} = 0$	
Body to drain diode reverse recovery time	t _{rr}	_	320	_	ns	$I_F = 7 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A}/\mu\text{s}$	

Note: 3. Pulse test

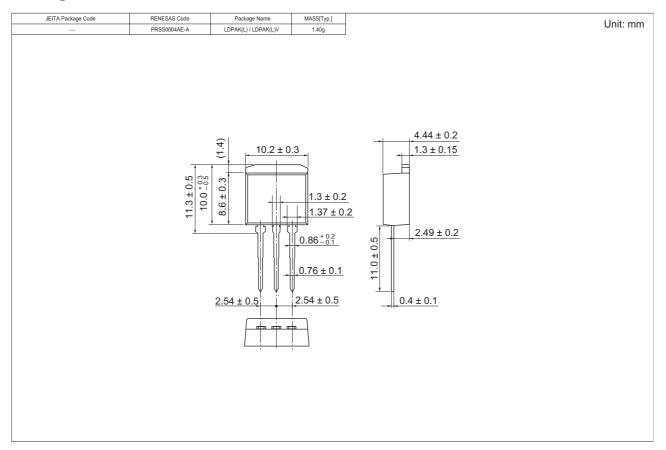
Main Characteristics

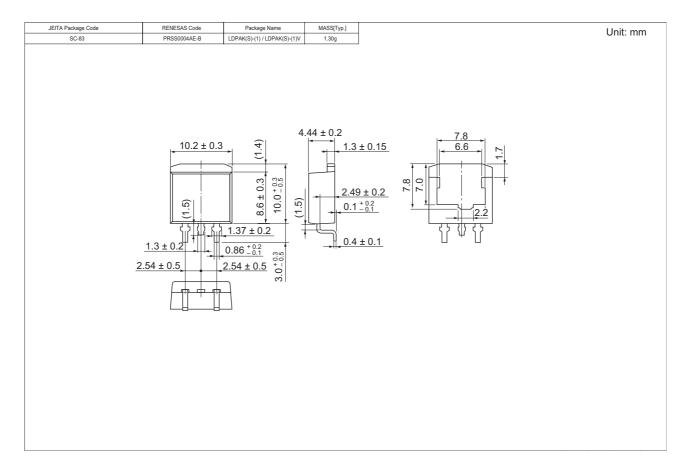






Package Dimensions





Ordering Information

Part Name	Quantity	Shipping Container
2SK1540L-E	500 pcs	Box (Sack)
2SK1540STL-E	1000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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